

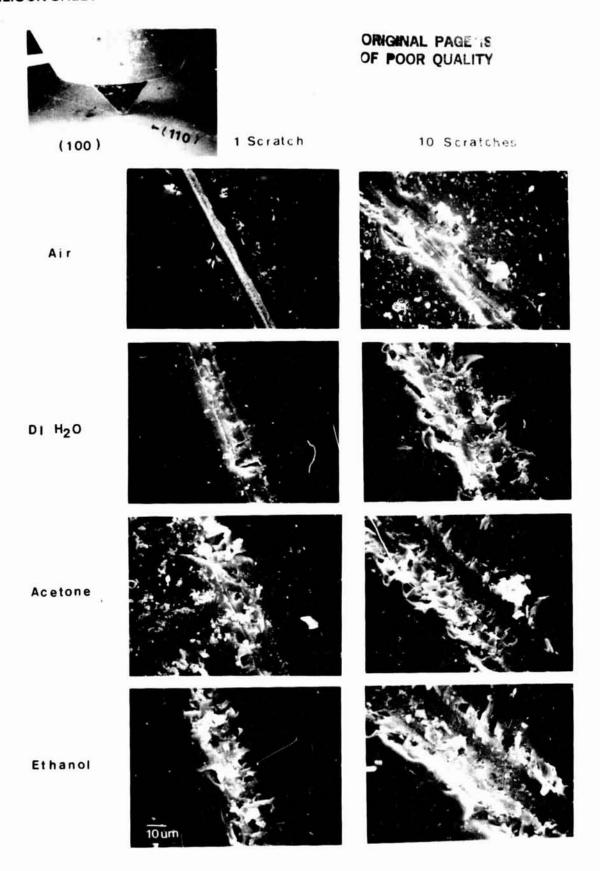
# N85-32441 SILICON SHEET SURFACE STUDIES

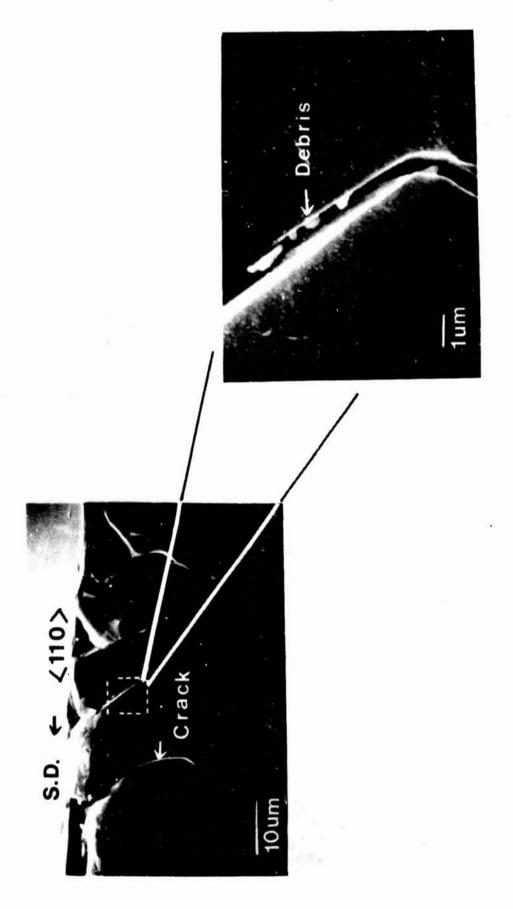
## UNIVERSITY OF ILLINOIS AT CHICAGO

#### S. Danyluk

# Relative Magnitudes of Residual Stresses in Web and Mobil Silicon Sheet

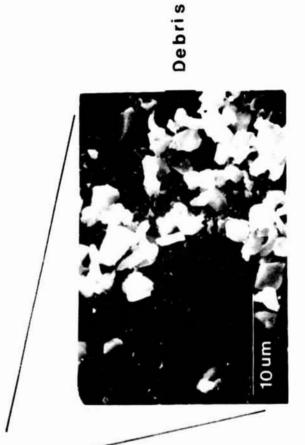
TECHNOLOGY	REPORT DATE October 2, 1984	
APPROACH Residual stresses in sheet silicon by interferometry. Simulation of abrasion of silicon by diamond by scratching and indentation tests. CONTRACTOR	STATUS  Developed an interferometry technique for measuring residual stresses in short, thin silicon sheet.  Measured the residual stresses in WEB and Mobil sheet.  Correlated experimental wear rate with a wear mode Determined the residual stresses due to scratching	
GOALS  Develop non-destructive residual stress measurement technique.  Determine wear mechanism in silicon.	Showed that dislocations are associated with scratching and indentations performed at room temperature.	





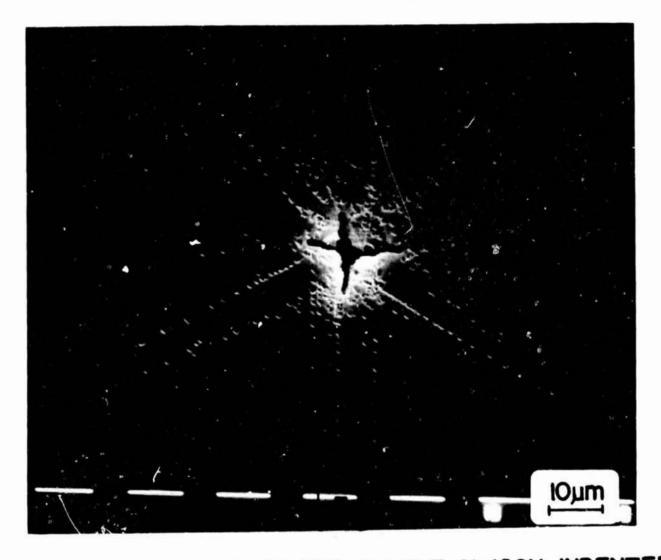
Deformation Plastic

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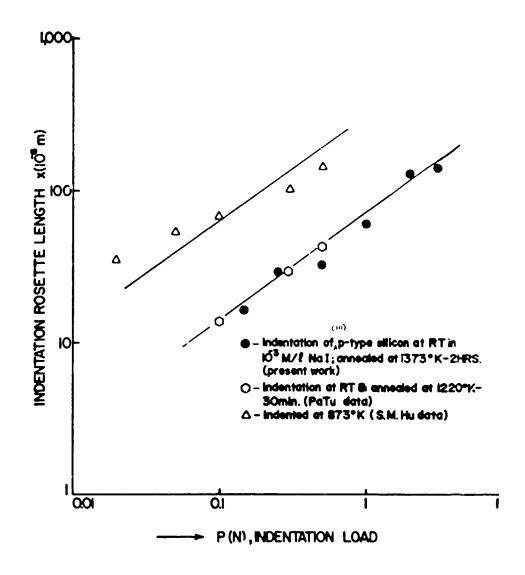


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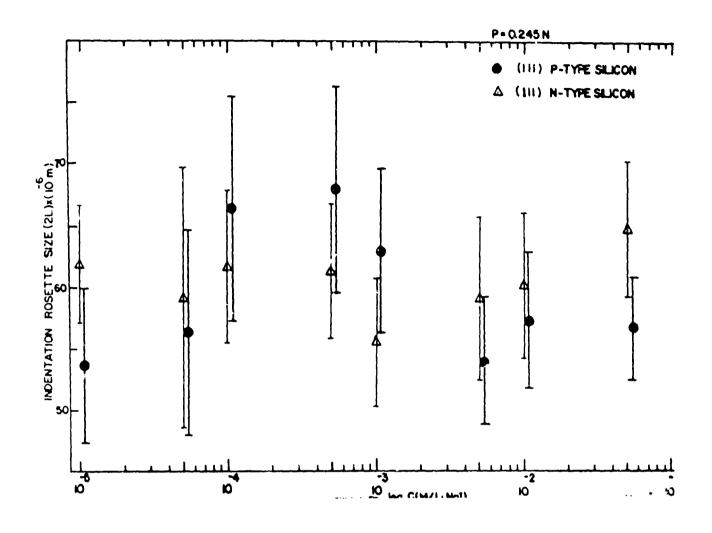
SILICON SHEET



SEM MICROGRAPH OF (III) P-TYPE SILICON INDENTED UNDER A LOAD OF .0.49N IN 103 M/L NaI; ANNEALED AT 1373 K-2HRS AND ETCHED IN DILUTE SIRTL SOLUTION.



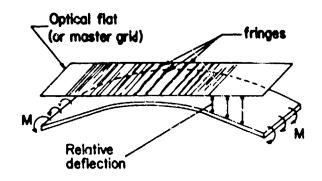


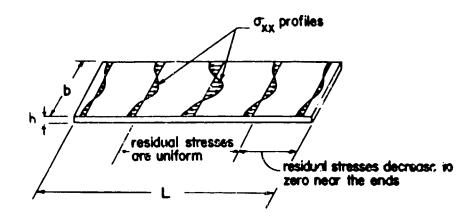


Later Market Contract

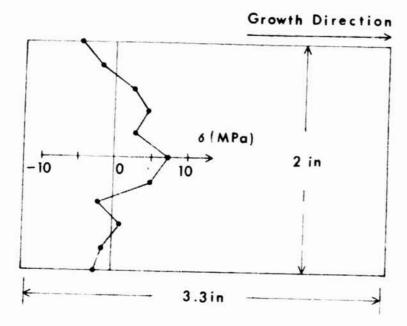


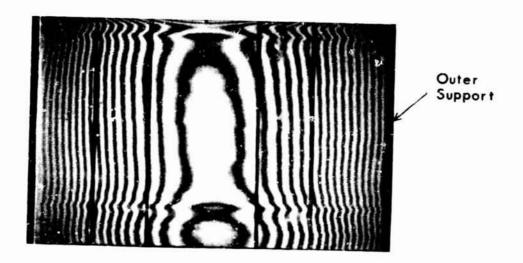
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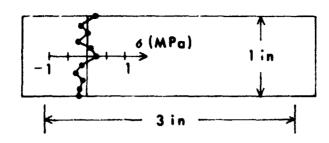
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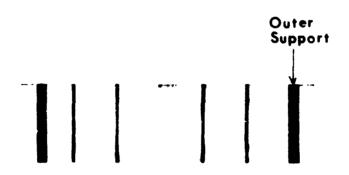




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		Sample No.	Magnitude of Maximum Residual Stress (MPa)	Growth Speed (cm/mm)
WEB	}	J515-2.3a	2.5	
	ì	J460-2.5a	0.4	
Mobil	,	47R1-1	9.0	2.00
	- }	- 2	5.0	2.00
	1	-3	7.3	1.75
	- {	-4	6.5	2.25

## **Problems and Concerns**

- 1. Do the residual stress measurements correlate with strain gauge measurements or dislocation distributions?
- 2. Is the fluid chemistry changed as a result of microcrack or dislocation generation?
- Does the abrasion mechanism change when abrasion speeds are high? What is the contact temperature.